

SuperMOS – TO-252 30V BV_{DSS} , 4m Ω $R_{DS(on)}$, N-channel MOSFET

1. Description

The KIA50N03BD-ES is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product KIA50N03BD-ES is Pb-free.

2. Features

- 30V, $R_{DS(ON)}=4m\Omega(Typ.) @V_{GS}=10V$
 $R_{DS(ON)}=6m\Omega(Typ.) @V_{GS}=4.5V$
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

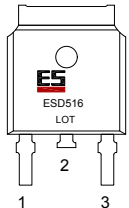
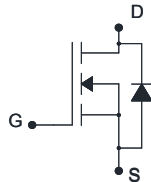
- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED!

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
KIA50N03BD-ES	TO-252	ESD516/LOT	Halogen free	Tape & Reel	2,500 PCS	UL 94V-0	13 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
1	Gate		
3	Source		
2	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C=25^{\circ}C$	I_D	65	A
	$T_C=75^{\circ}C$		50	
Maximum Power Dissipation	$T_C=25^{\circ}C$	P_D	42	W
	$T_C=75^{\circ}C$		25	
Pulsed Drain Current ^a		I_{DM}	260	A
Avalanche Current, Single Pulsed ^b		I_{AS}	32	A
Avalanche Energy, Single Pulsed ^b		E_{AS}	153	mJ
Operating Junction Temperature		T_J	150	°C
Lead Temperature		T_L	260	°C
Storage Temperature Range		T_{stg}	-55 to 150	°C

Thermal resistance ratings

Single Operation				
Parameter		Symbol	Typical	Unit
Junction-to-Case Thermal Resistance	$t \leq 10$ s	$R_{\theta JC}$	3	°C/W

Note:

a: Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu s$, Duty Cycle=1%

b: $T_J=25^{\circ}C$, $V_{DD}=30V$, $V_G=10V$, $L=0.3mH$, $R_g=25\Omega$

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1.0	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.75	2.5	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		4.0	6.5	m Ω
		$V_{GS}=4.5V, I_D=20A$		6.0	8.5	
Forward Trans conductance	g_{FS}	$V_{DS}=5.0V, I_D=20A$			60	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz, V_{DS}=25V$		1036		pF
Output Capacitance	C_{OSS}			444		
Reverse Transfer Capacitance	C_{RSS}			62		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=10V, V_{DS}=15V, I_D=20A$		15.8		nC
Gate-to-Source Charge	Q_{GS}			3.3		
Gate-to-Drain Charge	Q_{GD}			3.6		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=10V, V_{DS}=15V, R_G=0.75\Omega, R_G=1.8\Omega$		5.5		ns
Rise Time	t_r			3.3		
Turn-Off Delay Time	$t_{d(OFF)}$			18		
Fall Time	t_f			4.3		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1.0A$		0.75	1.5	V

7. Typical Characteristic

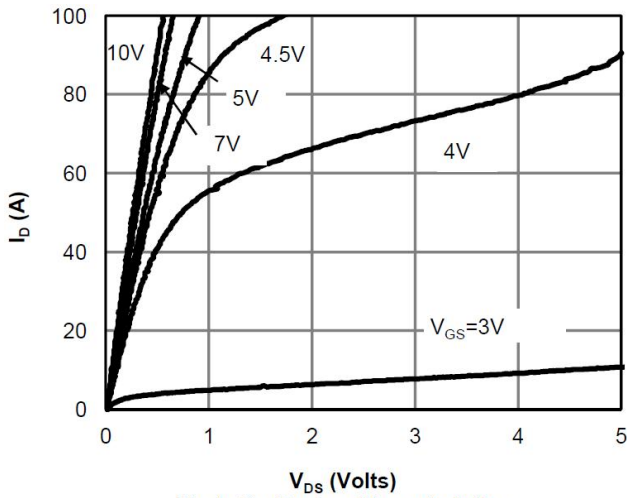


Fig 1: On-Region Characteristics

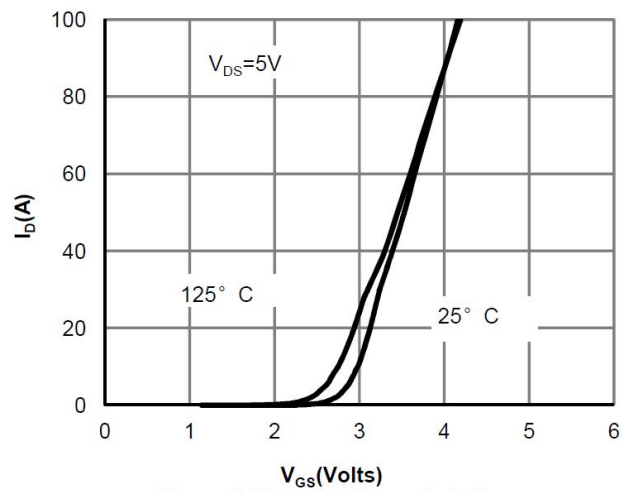


Figure 2: Transfer Characteristics

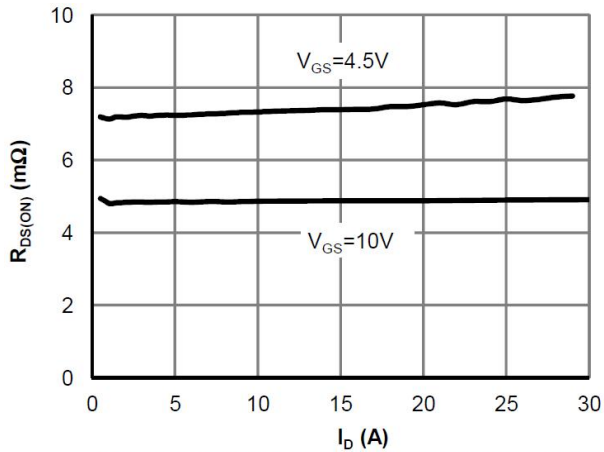


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

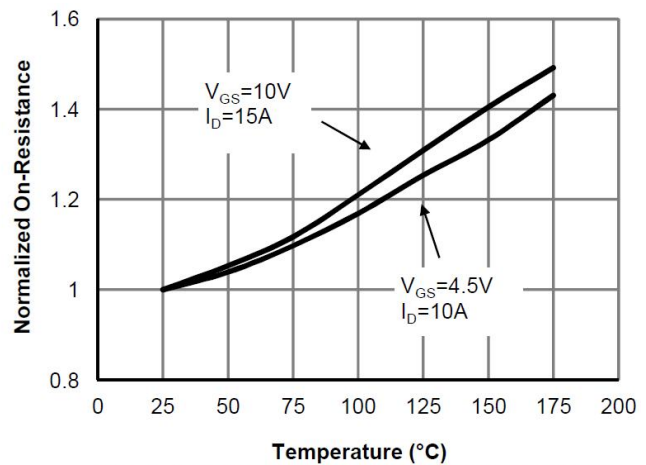


Figure 4: On-Resistance vs. Junction Temperature

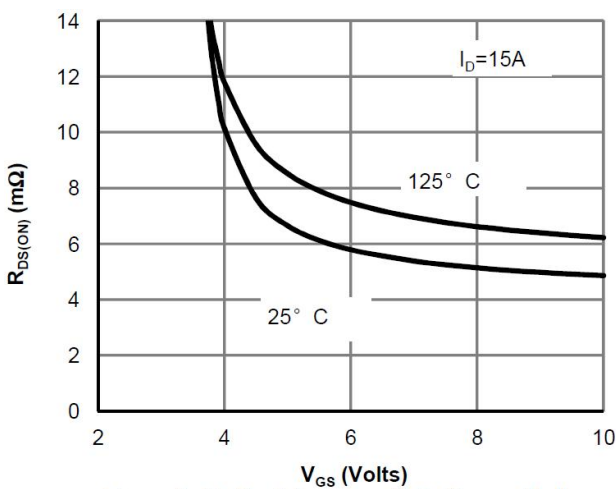


Figure 5: On-Resistance vs. Gate-Source Voltage

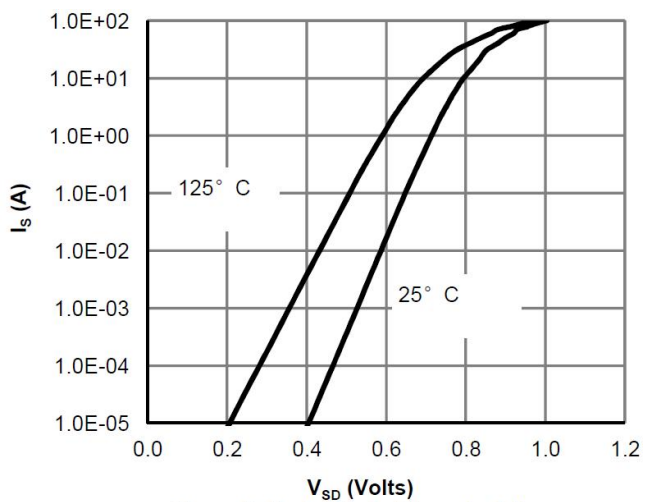


Figure 6: Body-Diode Characteristics

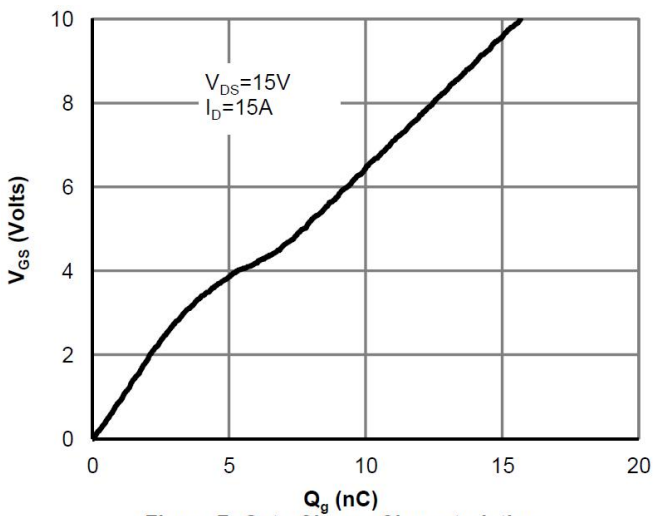


Figure 7: Gate-Charge Characteristics

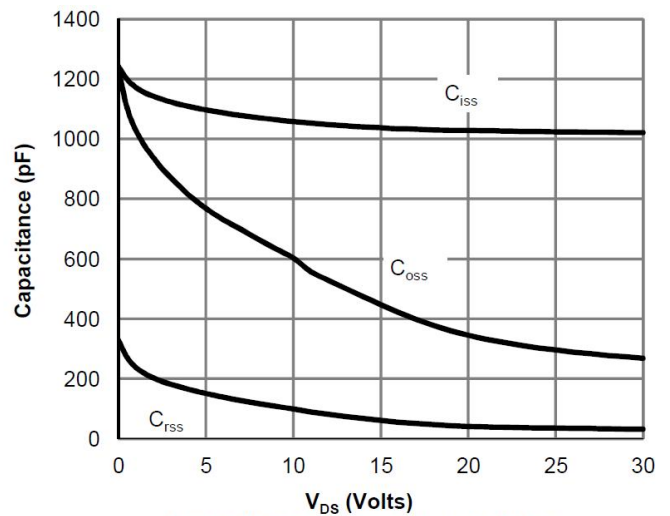


Figure 8: Capacitance Characteristics

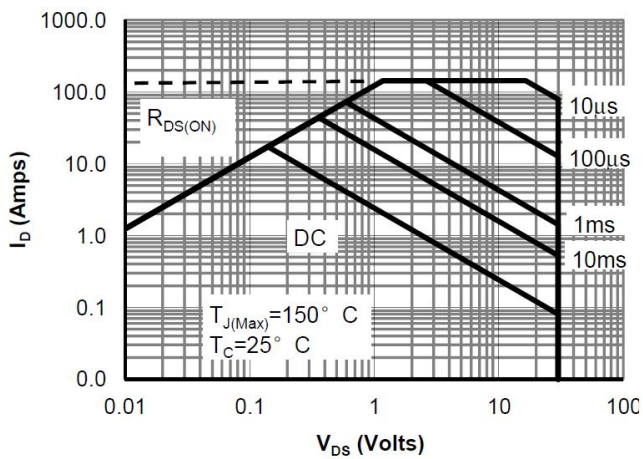


Figure 9: Maximum Forward Biased Safe Operating Area

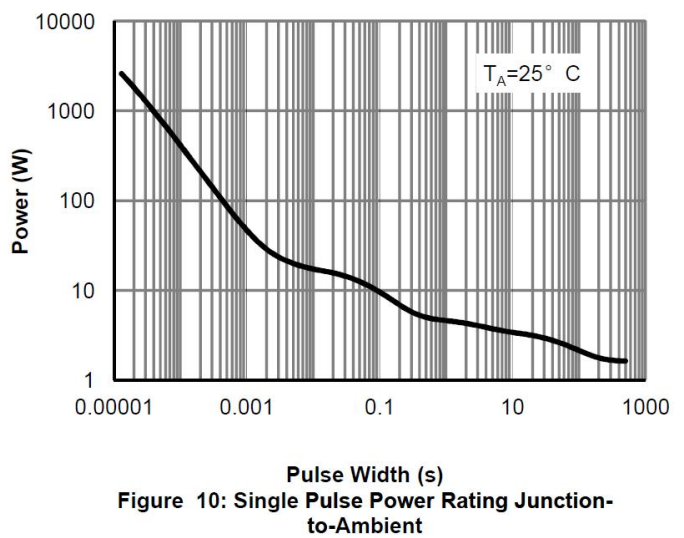


Figure 10: Single Pulse Power Rating Junction-to-Ambient

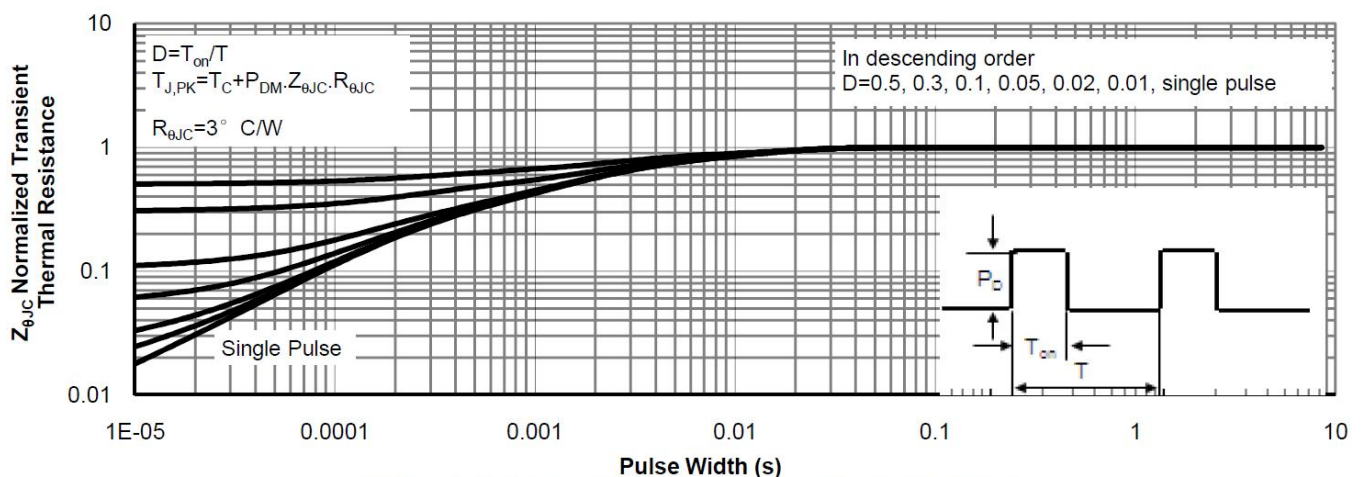
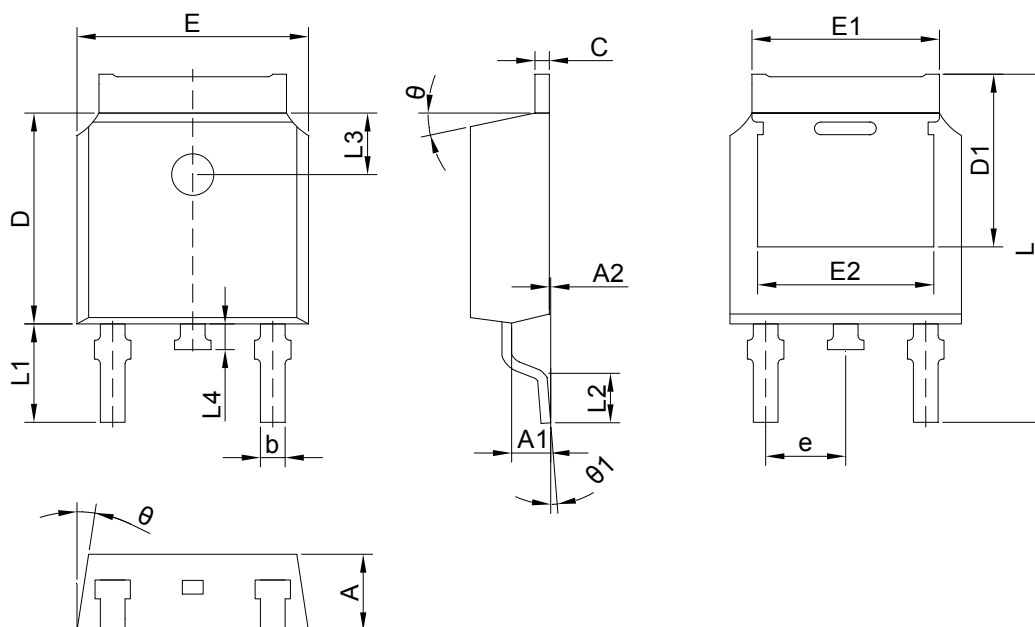


Figure 11: Normalized Maximum Transient Thermal Impedance

8. Dimension (TO-252)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER							
SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	2.10	2.30	2.50	E2	4.63	4.83	5.03
A1	0.97	1.07	1.17	L	9.90	10.10	10.30
A2	0.00	-	0.12	L1	2.74	2.94	3.14
b	0.66	0.76	0.86	L2	1.40	1.50	1.70
C	0.45	0.51	0.60	L3	1.65	1.80	1.95
D	5.90	6.10	6.30	L4	0.60	0.80	1.00
D1	5.10	5.30	5.45	e	2.286 BSC		
E	6.40	6.60	6.80	theta	5°	7°	10°
E1	5.10	5.33	5.45	theta1	0°	-	3°

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